

MAPLST1617-030CF



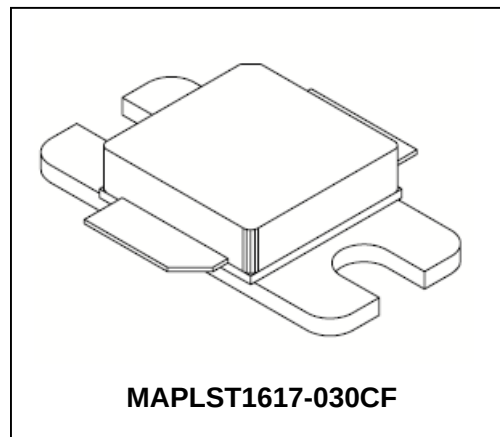
LDMOS RF Line Power FET Transistor
30 W , 1600-1700 MHz, 28V

Discontinued
(For Reference Only)

Product Image

Designed for INMARSAT applications in the 1620-1670 MHz frequency band.

- Typical two tone performance (IMD=-30 dBc):
Average output power: 15W
Gain: 14dB (typ.)
Efficiency: 38% (typ.)
- 10:1 VSWR ruggedness at 30W, 28V, 1670MHz)



MAXIMUM RATINGS

Parameter	Symbol	Rating	Units
Drain—Source Voltage	V_{DS}	65	V _{dc}
Gate—Source Voltage	V_{GS}	20	V _{dc}
Total Power Dissipation @ T _C = 25 °C	P _D	97	W
Storage Temperature	T _{STG}	-40 to +150	°C
Junction Temperature	T _J	+200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _{θJC}	1.8	°C/W

NOTE—**CAUTION**—MOS devices are susceptible to damage from electrostatic charge. Precautions in handling and packaging MOS devices should be observed.

LDMOS RF Line Power FET Transistor
30 W , 1600-1700 MHz, 28V

Discontinued
(For Reference Only)

Characteristic	Symbol	Min	Typ	Max	Unit
DC CHARACTERISTICS @ 25°C					
Drain-Source Breakdown Voltage ($V_{GS} = 0$ Vdc, $I_D = 20$ μ Adc)	$V_{(BR)DSS}$	65	—	—	Vdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28$ Vdc, $V_{GS} = 0$)	I_{DSS}	—	—	1	μ Adc
Gate—Source Leakage Current ($V_{GS} = 5$ Vdc, $V_{DS} = 0$)	I_{GSS}	—	—	1	μ Adc
Gate Threshold Voltage ($V_{DS} = 10$ Vdc, $I_D = 1$ mA)	$V_{GS(th)}$	2	—	4	Vdc
Gate Quiescent Voltage ($V_{DS} = 28$ Vdc, $I_D = 250$ mA)	$V_{DS(Q)}$	2	—	4.5	Vdc
Drain-Source On-Voltage ($V_{GS} = 10$ Vdc, $I_D = 1$ A)	$V_{DS(on)}$	—	0.2	—	Vdc
Forward Transconductance ($V_{GS} = 10$ Vdc, $I_D = 1$ A)	Gm	—	1.2	—	S
DYNAMIC CHARACTERISTICS @ 25°C					
Input Capacitance (Including Input Matching Capacitor in Package) ($V_{DS} = 28$ Vdc, $V_{GS} = 0$, $f = 1$ MHz)	C_{iss}	—	90	—	pF
Output Capacitance ($V_{DS} = 28$ Vdc, $V_{GS} = 0$, $f = 1$ MHz)	C_{oss}	—	32.5	—	pF
Reverse Transfer Capacitance ($V_{DS} = 28$ Vdc, $V_{GS} = 0$, $f = 1$ MHz)	C_{rss}	—	1.5	—	pF
RF FUNCTIONAL TESTS @ 25°C (In M/A-COM Test Fixture)					
CW Gain ($V_{DS} = 28$ Vdc, $P_{OUT} = 30$ W (avg.), $I_{DQ} = 250$ mA, $f_0 = 1670$ MHz)	G_{ps}	—	14	—	dB
CW Drain Efficiency ($V_{DS} = 28$ Vdc, $P_{OUT} = 30$ W (avg.), $I_{DQ} = 250$ mA, $f_0 = 1670$ MHz)	EFF (η)	—	50	—	%
CW Input Return Loss ($V_{DS} = 28$ Vdc, $P_{OUT} = 30$ W (avg.), $I_{DQ} = 250$ mA, $f_0 = 1670$ MHz)	IRL	—	-10	-9	dB
IMD ($V_{DS} = 28$ Vdc, $P_{OUT} = 15$ W (avg.) (30 W PEP), $I_{DQ} = 250$ mA, $f_0 = 1670$ MHz, $f_1 = 1670.1$ MHz)	IMD	—	-30	—	dBc
Output VSWR Tolerance ($V_{DS} = 28$ Vdc, $P_{OUT} = 30$ W (avg.), $I_{DQ} = 250$ mA, $f_0 = 1670$ MHz)	Ψ	No Degradation In Output Power Before and After Test			

(1) Device specifications obtained on a Production Test Fixture.

LDMOS RF Line Power FET Transistor
30 W , 1600-1700 MHz, 28V

Discontinued
(For Reference Only)

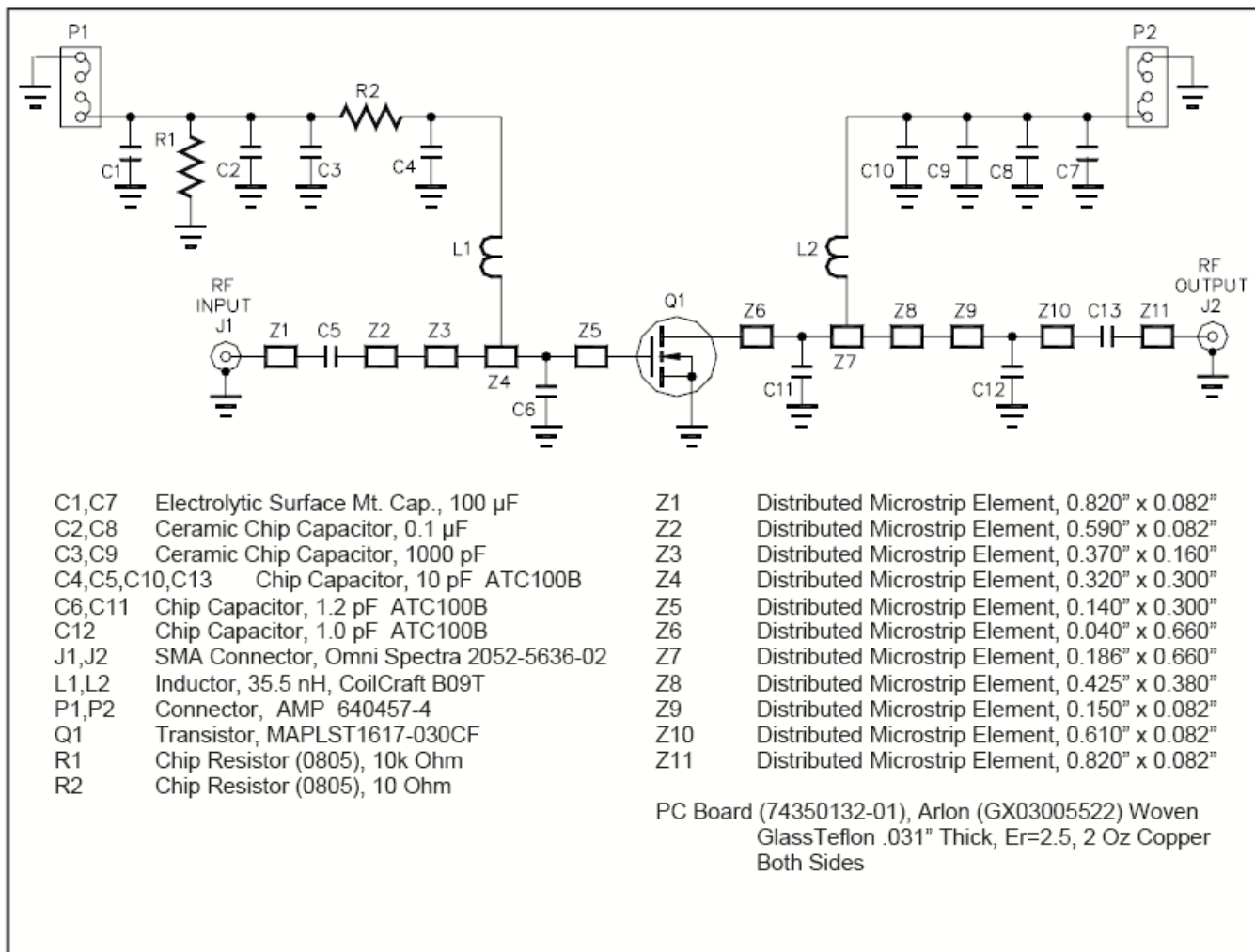


FIGURE 1. 1620—1670 MHZ TEST FIXTURE SCHEMATIC

LDMOS RF Line Power FET Transistor
30 W , 1600-1700 MHz, 28V

Discontinued
(For Reference Only)

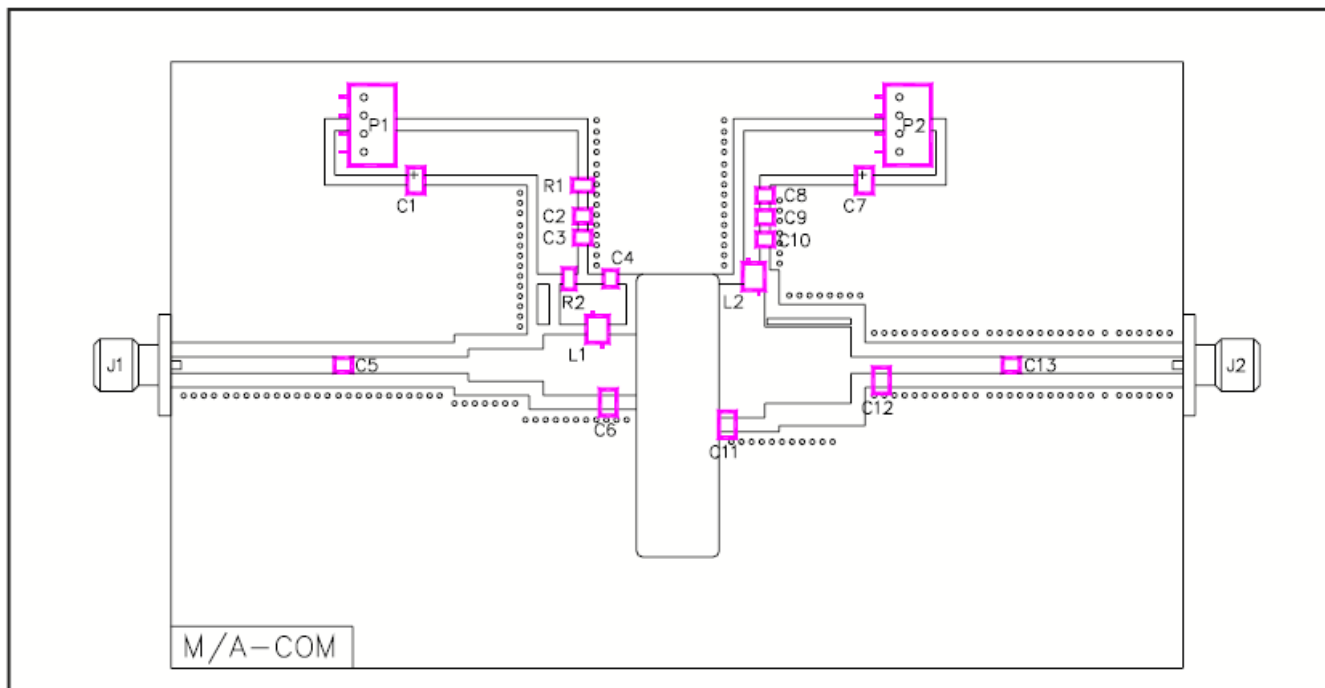
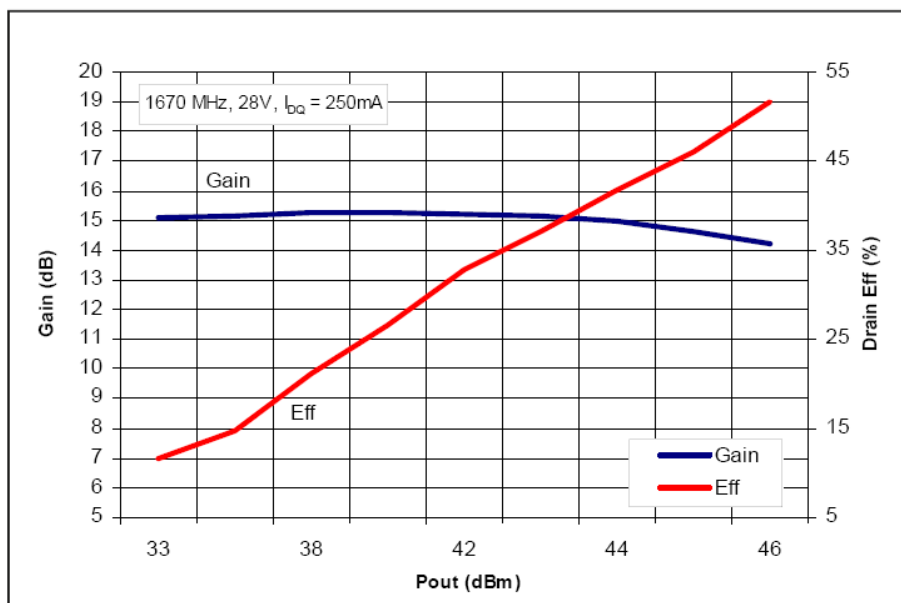


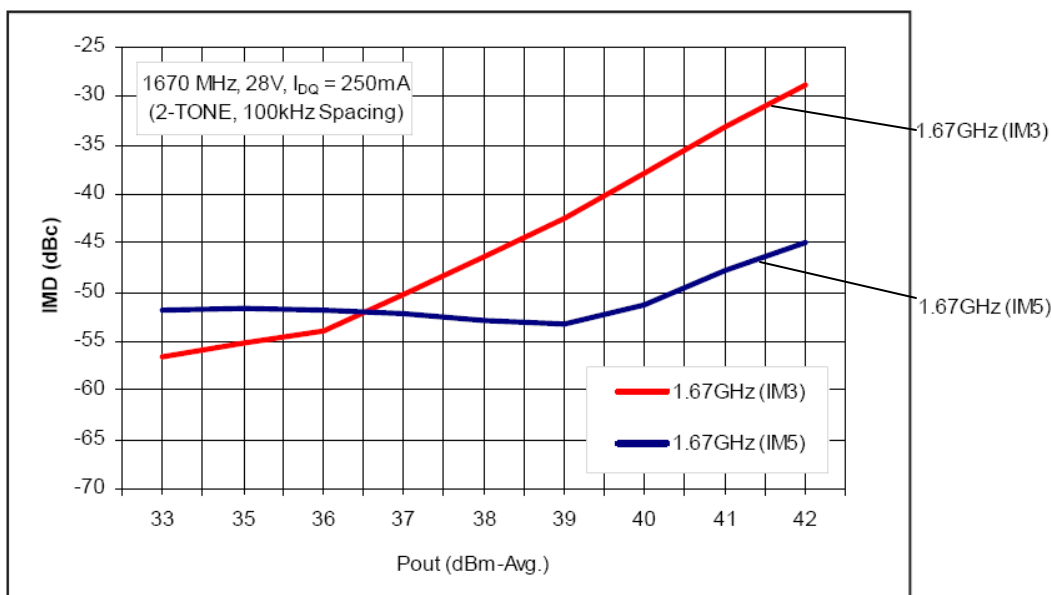
FIGURE 2. 1620—1670 MHz TEST FIXTURE COMPONENT LAYOUT

LDMOS RF Line Power FET Transistor
30 W , 1600-1700 MHz, 28V

Discontinued
(For Reference Only)



GRAPH 1. CW: GAIN AND EFFICIENCY VS. OUTPUT POWER



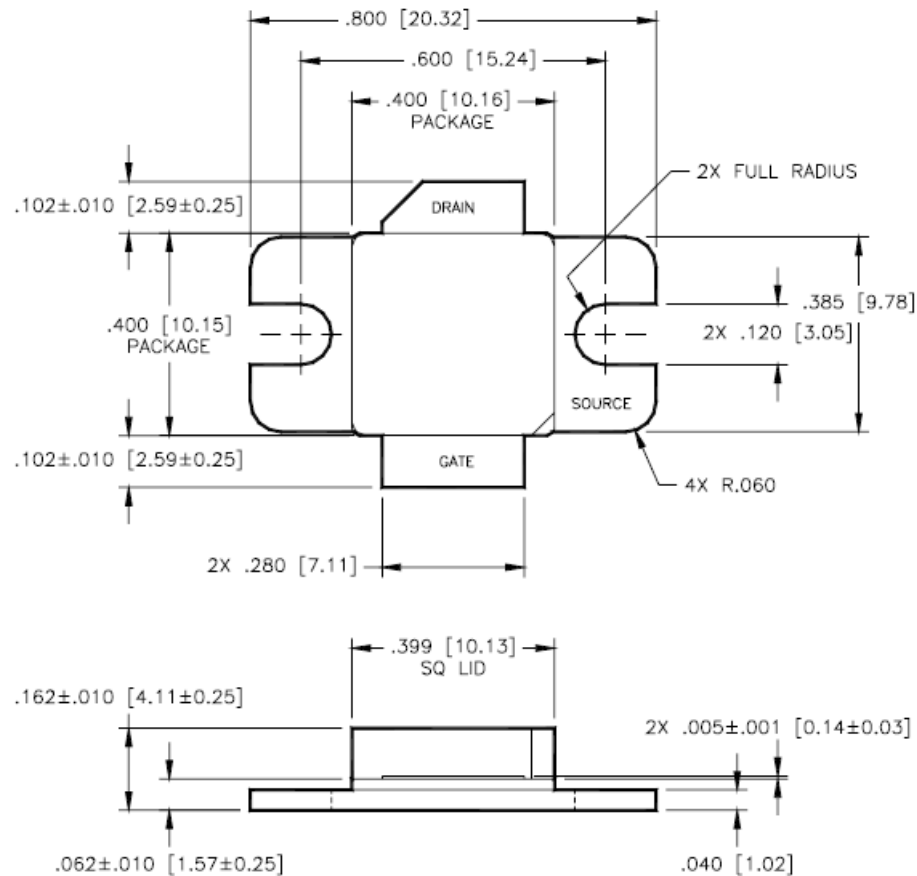
GRAPH 2. TWO TONE: INTERMODULATION DISTORTION VS. OUTPUT POWER

LDMOS RF Line Power FET Transistor

30 W , 1600-1700 MHz, 28V

Discontinued
(For Reference Only)

PACKAGE DIMENSIONS



UNLESS OTHERWISE NOTED, TOLERANCES ARE
INCHES ± 0.005 " [MILLIMETERS ± 0.13 MM]